74AUP1G240

Low-power inverting buffer/line driver; 3-state Rev. 4 — 29 June 2012

Product data sheet

General description 1.

The 74AUP1G240 provides the single inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (OE). A HIGH level at pin OE causes the output to assume a high-impedance OFF-state.

This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input OE is HIGH.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- Input-disable feature allows floating input conditions
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G240GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G240GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74AUP1G240GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74AUP1G240GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1G240GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202
74AUP1G240GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226

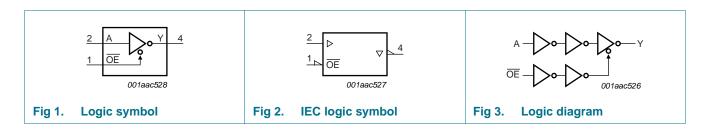
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G240GW	p2
74AUP1G240GM	p2
74AUP1G240GF	p2
74AUP1G240GN	p2
74AUP1G240GS	p2
74AUP1G240GX	p2

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description			
	TSSOP5 and X2SON5	XSON6				
ŌĒ	1	1	output enable input			
Α	2	2	data input			
GND	3	3	ground (0 V)			
Υ	4	4	data output			
n.c.	-	5	not connected			
V _{CC}	5	6	supply voltage			

7. Functional description

Table 4. Function table[1]

Input OE		
OE	A	Υ
L	L	Н
L	Н	L
Н	X	Z

^[1] H = HIGH voltage level;

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		3 7 8		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2] _	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

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L = LOW voltage level;

X = Don't care;

Z = high-impedance OFF-state.

^[2] For TSSOP5 packages: above 87.5 $^{\circ}$ C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON5 packages: above 118 $^{\circ}$ C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I _I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ

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Low-power inverting buffer/line driver; 3-state

Static characteristics ...continued Table 7. At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Δl _{CC}	additional supply current	data input; V _I = V _{CC} $-$ 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1] -	-	40	μΑ
		$\overline{\text{OE}}$ input; $V_{\text{I}} = V_{\text{CC}} - 0.6 \text{ V}$; $I_{\text{O}} = 0 \text{ A}$; $V_{\text{CC}} = 3.3 \text{ V}$	[1] -	-	110	μΑ
	$\begin{array}{c} V_{CC} = 3.3 \ V \\ \hline OE input, V_1 = V_{CC} - 0.6 \ V; \ V_0 = 0 \ A; \ V_1 = 0 \ A; \ V_2 = 0.3 \ V \\ \hline OE = V_{CC}; \ V_{CC} = 0.8 \ V to 3.6 \ V; \\ \hline OE = V_{CC}; \ V_{CC} = 0.8 \ V to 3.6 \ V; \\ \hline OE = V_{CC}; \ V_{CC} = 0.8 \ V to 3.6 \ V; \\ \hline OE = V_{CC}; \ V_{CC} = 0.8 \ V to 3.6 \ V; \\ \hline OE = V_{CC}; \ V_{CC} = 0.8 \ V to 3.6 \ V; \\ \hline OUTPUT CAPACITAINCE & 0.8 \ V & 0.000 \ V_{CC} & 0.8 \ V \\ \hline OUTPUT CAPACITAINCE & 0.8 \ V & 0.000 \ V_{CC} & 0.8 \ V \\ \hline OUTPUT CAPACITAINCE & 0.8 \ V & 0.000 \ V_{CC} & 0.8 \ V \\ \hline OUTPUT CAPACITAINCE & 0.8 \ V & 0.000 \ V_{CC} & 0.8 \ V \\ \hline V_{CC} = 0.9 \ V to 1.95 \ V & 0.665 \ V_{CC} & 0.8 \\ \hline V_{CC} = 0.9 \ V to 1.95 \ V & 0.665 \ V_{CC} & 0.8 \\ \hline V_{CC} = 0.9 \ V to 1.95 \ V & 0.665 \ V_{CC} & 0.8 \\ \hline V_{CC} = 0.9 \ V to 1.95 \ V & 0.665 \ V_{CC} & 0.8 \\ \hline V_{CC} = 0.8 \ V & 0.000 \ V_{CC} & 0.8 \\ \hline V_{CC} = 0.9 \ V to 1.95 \ V & 0.000 \ V_{CC} & 0.000 \ V_{C$	1	μΑ			
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	8.0	-	pF
Co	output capacitance					
	output enabled	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF
	output disabled	V_{CC} = 0 V to 3.6 V; V_{O} = GND or V_{CC}	-	1.5	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	0.70 × \	′cc -	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V	′cc -	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
V _{OH} I		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$V_{CC} - 0$.1 -	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{C}$	c -	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		$I_O = 2.3 \text{ mA}$; $V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
			-	-		V
l _l	input leakage current	$V_1 = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
I _{OZ}	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$		_	±0.5	μΑ

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V		-	-	±0.6	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$		-	-	0.9	μΑ
Δl _{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	[1]	-	-	50	μΑ
		$\overline{\text{OE}}$ input; $V_{\text{I}} = V_{\text{CC}} - 0.6 \text{ V}$; $I_{\text{O}} = 0 \text{ A}$; $V_{\text{CC}} = 3.3 \text{ V}$	[1]	-	-	120	μΑ
		all inputs; $V_1 = GND$ to 3.6 V; $\overline{OE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	[2]	-	-	1	μΑ
Γ _{amb} = -	40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V		$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V		$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V		-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V		-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V		-	-	0.9	V
V _{OH} I	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$		V _{CC} - 0.11	-	-	٧
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		$0.6 \times V_{CC}$	-	-	٧
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		0.93	-	-	٧
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.67	-	-	٧
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.40	- 0.9 - 50 - 120 - 120 - 1 - 1 - 1	V	
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.30	-	- - - - 0.25 × V _{CC} 0.30 × V _{CC} 0.7 0.9 - - - - - - - - - - - - - - - - - - -	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V		-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.50	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μΑ
oz	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V		-	-	±0.75	μΑ

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> _	-	75	μΑ
		$\overline{\text{OE}}$ input; $V_{\text{I}} = V_{\text{CC}} - 0.6 \text{ V}$; $I_{\text{O}} = 0 \text{ A}$; $V_{\text{CC}} = 3.3 \text{ V}$	<u>[1]</u> -	-	180	μΑ
		all inputs; $V_I = GND$ to 3.6 V; $\overline{OE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	[2] -	-	1	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +1	25 °C	Unit
			Mi	'n	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F		'	'			•		'	
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$	-		22.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.	0	5.8	12.6	2.8	14.1	15.5	ns
		V_{CC} = 1.4 V to 1.6 V	2.	3	4.0	7.3	2.1	8.5	9.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.	0	3.2	5.5	1.9	6.7	7.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.	8	2.6	4.1	1.5	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.	4	2.3	3.6	1.3	4.1	4.6	ns
t _{en}	enable time	OE to Y; see Figure 9	[3]							
		$V_{CC} = 0.8 \text{ V}$	-		70.2	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.	1	6.4	14.3	2.8	15.9	17.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.	5	4.4	8.1	2.2	9.5	10.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.	1	3.6	6.2	1.9	7.4	8.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.	8	2.8	4.6	1.7	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.	7	2.5	4.0	1.7	4.7	5.3	ns
t _{dis}	disable time	OE to Y; see Figure 9	<u>[4]</u>							
		$V_{CC} = 0.8 \text{ V}$	-		14.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.	0	4.3	7.4	2.3	8.3	9.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.	6	3.2	5.2	1.7	5.9	6.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.	5	3.0	4.8	1.5	5.5	6.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.	1	2.2	3.5	1.4	4.0	4.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.	3	2.5	3.9	1.4	4.5	5.0	ns

^[2] To show I_{CC} remains very low when the input-disable feature is enabled.

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 10</u>

Symbol	Parameter	Conditions			25 °C		-40	0 °C to +1	25 °C	Uni
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 10	ρF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	25.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	6.6	14.5	3.2	16.3	18.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	4.6	8.4	2.0	9.9	10.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	3.8	6.4	1.8	7.7	8.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.1	4.8	1.7	5.7	6.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.7	2.8	4.3	1.7	5.0	5.5	ns
t _{en}	enable time	OE to Y; see Figure 9	[3]							
		$V_{CC} = 0.8 V$		-	74.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	7.4	16.3	3.2	18.2	20.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	5.1	9.2	2.1	10.9	12.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	4.1	7.1	1.8	8.5	9.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.4	5.4	1.7	6.4	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	3.1	4.8	1.7	5.7	6.3	ns
t _{dis} c	disable time	OE to Y; see Figure 9	<u>[4]</u>							
		$V_{CC} = 0.8 V$		-	33.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.4	5.4	9.0	3.2	10.0	11.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	4.1	6.3	2.1	7.1	7.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.3	4.2	6.3	1.8	7.1	7.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.0	4.6	1.7	5.2	5.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	3.8	5.7	1.7	6.4	7.1	ns
C _L = 15	ρF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	29.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.9	7.4	16.3	3.6	18.4	20.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.1	9.4	2.5	11.1	12.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.2	4.2	7.2	2.1	8.7	9.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	3.5	5.4	1.9	6.5	7.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.0	3.3	4.9	1.9	5.7	6.4	ns
t _{en}	enable time	OE to Y; see Figure 9	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	77.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.0	8.2	18.2	3.6	20.4	22.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.6	10.3	2.5	12.2	13.4	ns
		V_{CC} = 1.65 V to 1.95 V		2.3	4.6	7.9	2.1	9.5	10.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	3.9	6.0	2.0	7.2	7.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	3.6	5.5	1.9	6.4	7.1	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{dis}	disable time	OE to Y; see Figure 9	<u>[4]</u>		'	'		•		
		$V_{CC} = 0.8 \text{ V}$		-	62.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.3	6.6	10.4	3.6	11.6	12.8	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	5.0	7.4	2.5	8.4	9.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.0	5.3	7.8	2.1	8.7	9.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.1	3.8	5.7	2.0	6.4	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.9	5.0	7.4	1.9	8.3	9.1	ns
C _L = 30	oF									
t _{pd} propagation delay		A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	39.1	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		5.0	9.7	21.6	4.6	24.3	26.8	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0	6.7	12.3	3.0	14.6	16.1	ns
	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.9	5.5	9.5	2.7	11.5	12.6	ns	
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	4.6	7.1	2.5	8.6	9.5	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.6	4.3	6.4	2.5	7.7	8.5	ns
t _{en} enable time		OE to Y; see Figure 9	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	89.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		5.2	10.6	23.8	4.6	26.7	29.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0	7.3	13.2	3.0	15.7	17.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.0	6.0	10.2	2.7	12.3	13.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.8	5.0	7.8	2.6	9.3	10.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.8	4.8	7.1	2.6	8.4	9.3	ns
t _{dis}	disable time	OE to Y; see Figure 9	[4]							
		$V_{CC} = 0.8 \text{ V}$		-	68.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		6.0	9.3	15.0	4.6	16.5	18.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.4	7.7	11.0	3.0	12.2	13.4	ns
		V_{CC} = 1.65 V to 1.95 V		5.1	8.8	12.4	2.7	13.7	15.1	ns
		V_{CC} = 2.3 V to 2.7 V		3.6	6.2	9.0	2.6	10.0	11.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.2	8.8	12.7	2.6	14.0	15.4	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)		
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[5]							
		$V_{CC} = 0.8 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.2	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.2	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}
- [3] t_{en} is the same as t_{PZH} and t_{PZL}
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ}
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

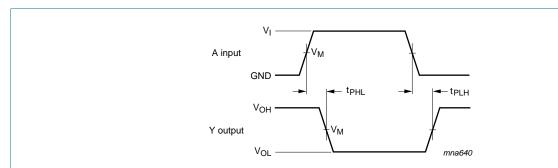
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	≤ 3.0 ns

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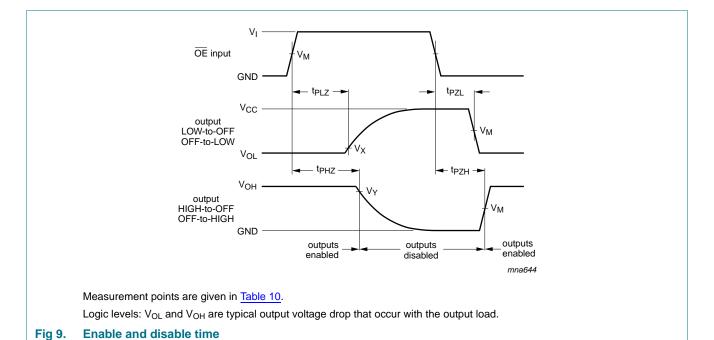
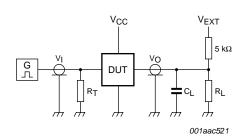


Table 10. Measurement points

Supply voltage	Input	Output				
V _{CC}	V _M	V _M	V _X	V _Y		
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.1 V	V _{OH} – 0.1 V		
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V		
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	V _{OH} – 0.3 V		

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Low-power inverting buffer/line driver; 3-state



Test data is given in Table 11.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 10. Test circuit for measuring switching times

Table 11. Test data

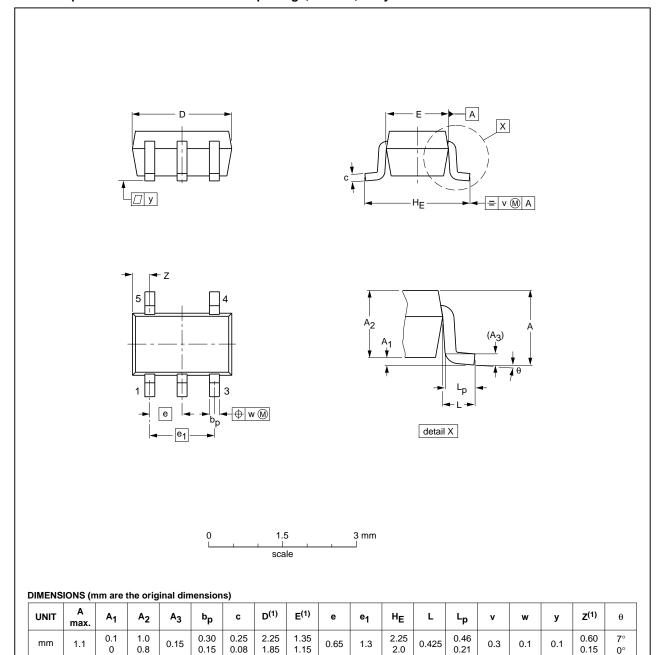
Supply voltage	Load	V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2\times V_{CC}$

[1] For measuring enable and disable times R_L = 5 k Ω , for measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



. .

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A		-00-09-01 03-02-19

Fig 11. Package outline SOT353-1 (TSSOP5)

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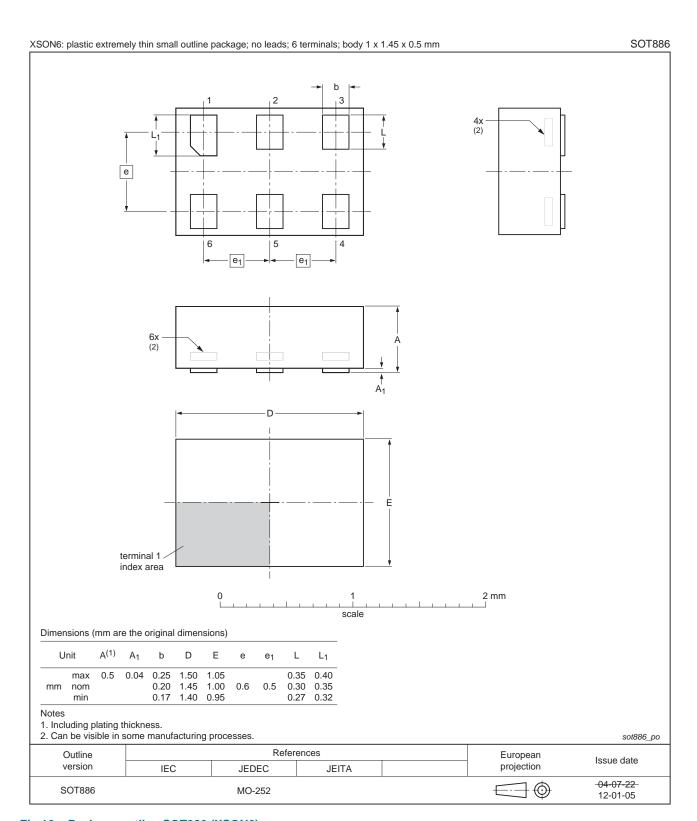


Fig 12. Package outline SOT886 (XSON6)

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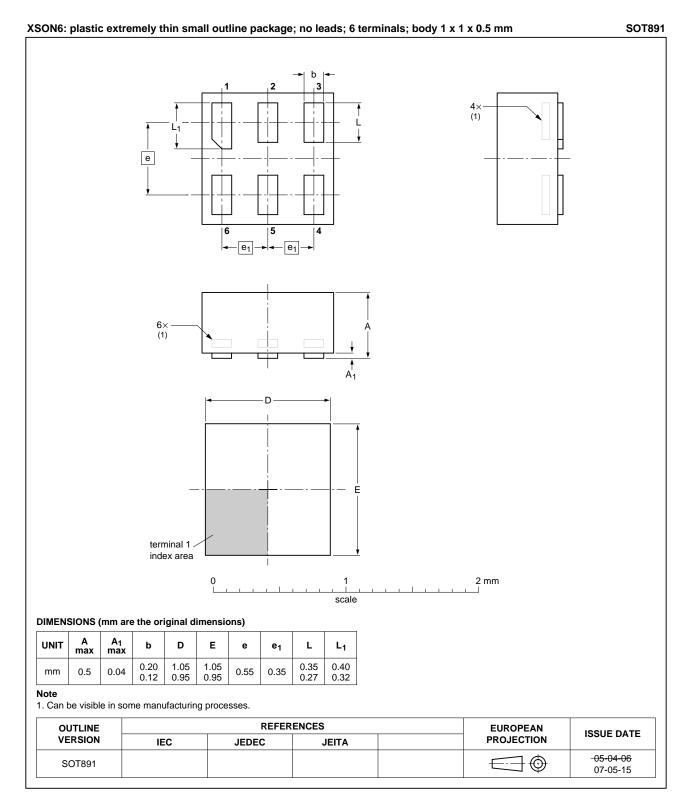


Fig 13. Package outline SOT891 (XSON6)

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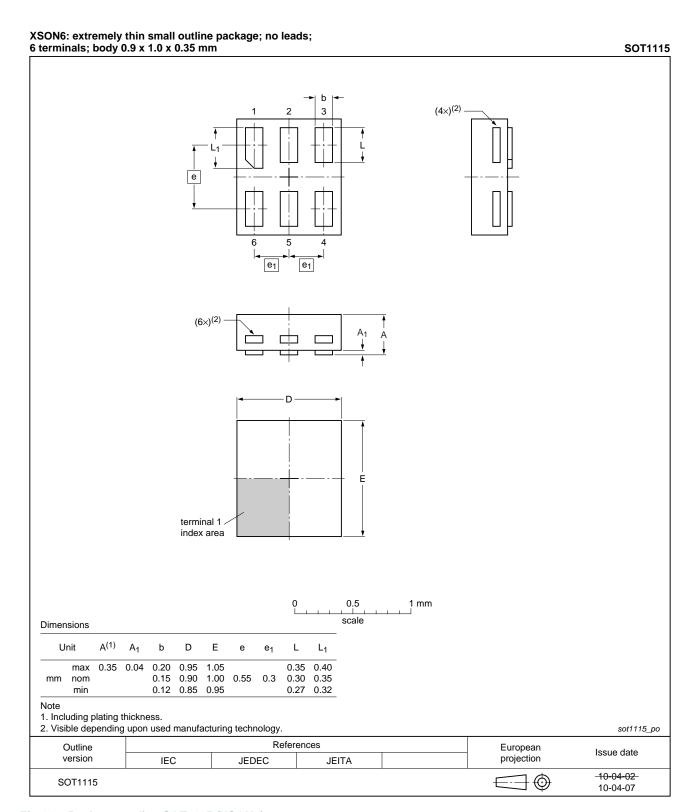


Fig 14. Package outline SOT1115 (XSON6)

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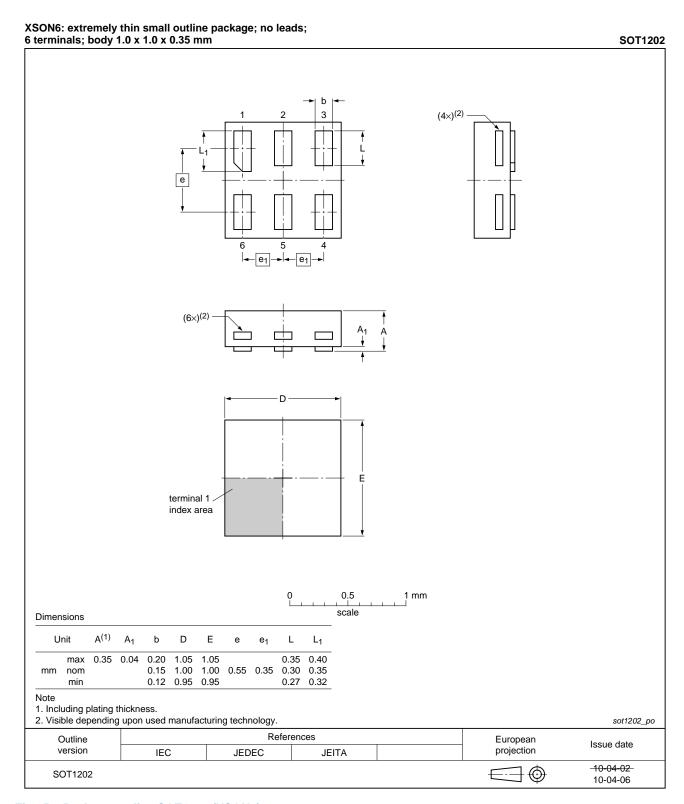


Fig 15. Package outline SOT1202 (XSON6)

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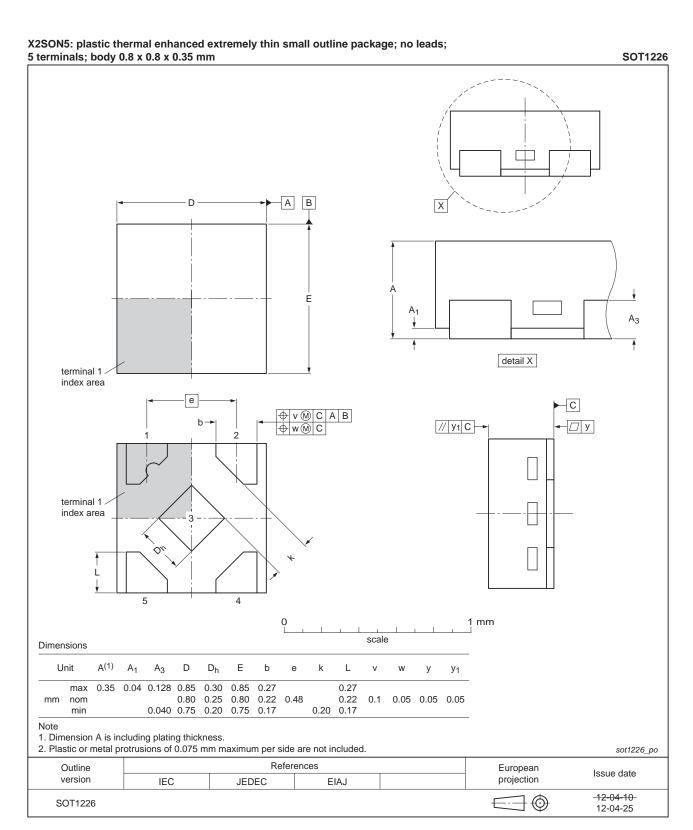


Fig 16. Package outline SOT1226 (X2SON5)

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14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G240 v.4	20120629	Product data sheet	-	74AUP1G240 v.3
Modifications:	 Added type 	number 74AUP1G240GX	(SOT1226)	
	 Package ou 	tline drawing of SOT886 (Figure 12) modified.	
74AUP1G240 v.3	20111124	Product data sheet	-	74AUP1G240 v.2
Modifications:	 Legal pages 	s updated.		
74AUP1G240 v.2	20100913	Product data sheet	-	74AUP1G240 v.1
74AUP1G240 v.1	20061106	Product data sheet	-	-

Product data sheet

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

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Low-power inverting buffer/line driver; 3-state

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